

GSDSR320 Series

Axial Lead Schottky Barrier Rectifiers

Product Description

Reverse Voltage 20V To 100V Forward Current 3.0A

Features

- Axial lead type devices for through hole design
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- Guard ring for over voltage protection
- Ultra high-speed switching
- Silicon epitaxial planar chip, metal silicon junction
- Lead-free parts meet environmental standards of MIL-STD-19500 /228

Mechanical Data

- Case : Molded plastic
- Epoxy : UL 94V-0 rate flame retardant
- Lead : Axial leads, solderable per MIL-STD-202, method 208 guaranteed
- Polarity : Color Band denotes cathode end
- Mounting position : Any
- Weight : 1.10 grams

Packages



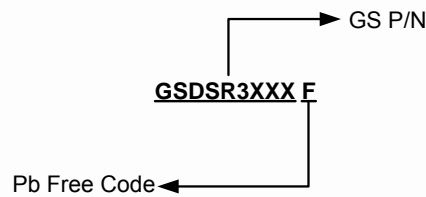
DO-201AD

Marking Information

Part Number	Package	Marking	Quantity
GSDSR320F	DO-201AD	WTYYWW SR320.	5000 PCS
GSDSR330F	DO-201AD	WTYYWW SR330.	
GSDSR340F	DO-201AD	WTYYWW SR340.	
GSDSR350F	DO-201AD	WTYYWW SR350.	
GSDSR360F	DO-201AD	WTYYWW SR360.	
GSDSR380F	DO-201AD	WTYYWW SR380.	
GSDSR3100F	DO-201AD	WTYYWW SR3100.	

- ※ "WT" GS Code & "YYWW" Date Code
- ※ "SR3XXX" GS P/N & "." Halogen Free

Ordering Information



Electrical Characteristics

Symbol	Conditions	SR320	SR330	SR340	SR350	SR360	Unit
V_{RRM}	Maximum Recurrent Peak Reverse Voltage	20	30	40	50	60	V
V_{RMS}	RMS Reverse Voltage	14	21	28	35	42	V
V_R	Maximum DC Blocking Voltage	20	30	40	50	60	V
V_F	Maximum Instantaneous Forward Voltage $I_F=3.0A$	0.55		0.70			V
C_J	Diode Junction Capacitance $f=1MHz$ and Applied 4V DC Reverse Voltage	300		250			pF
Symbol	Conditions	SR380		SR3100		Unit	
V_{RRM}	Maximum Recurrent Peak Reverse Voltage	80		100		V	
V_{RMS}	RMS Reverse Voltage	56		70		V	
V_R	Maximum DC Blocking Voltage	80		100		V	
V_F	Maximum Instantaneous Forward Voltage $I_F=3.0A$	0.85				V	
C_J	Diode Junction Capacitance $f=1MHz$ and Applied 4V DC Reverse Voltage	250				pF	
I_R	Maximum DC Reverse Current At Rated DC Blocking Voltage	$T_A=25^\circ C$	1.0				mA
		$T_A=100^\circ C$	30				
$I_{F(AV)}$	Maximum Average Forward Rectified Current See (Fig.1)	3.0				A	
I_{FSM}	Peak Forward Surge Current, 8.3ms Single Half Sine-Wave Superimposed on Rated Load(JEDEC Method)	80				A	
$R_{\theta JA}$	Thermal Resistance	50				$^\circ C/W$	
T_J	Junction Temperature Range	-65 to +150				$^\circ C$	
T_{STG}	Storage Junction Temperature Range	-65 to +150				$^\circ C$	

Typical Characteristics

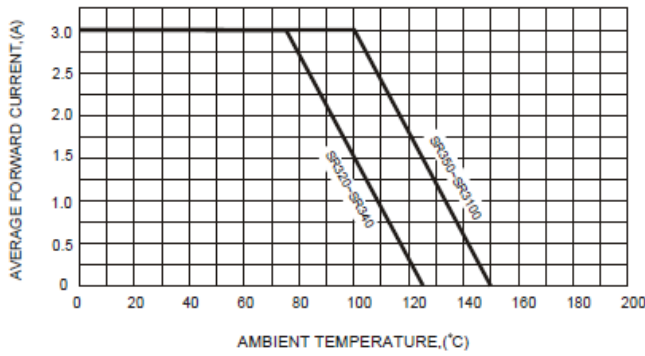


FIG.1-TYPICAL FORWARD CURRENT DERATING CURVE

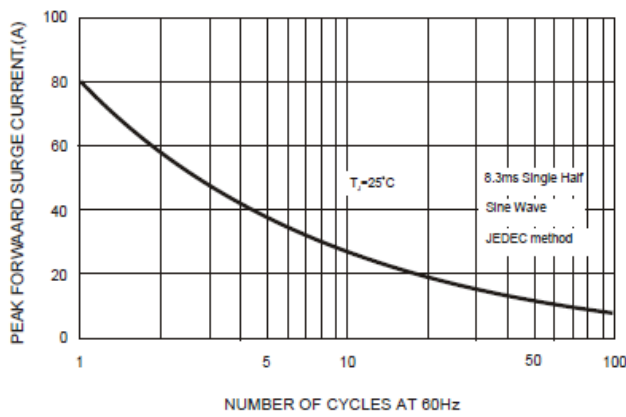


FIG.3-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

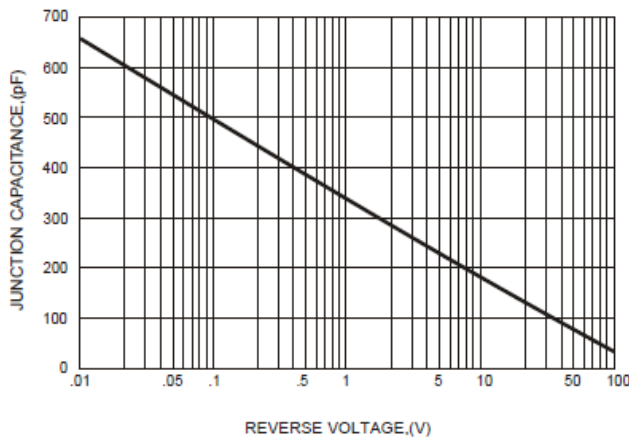


FIG.4-TYPICAL JUNCTION CAPACITANCE

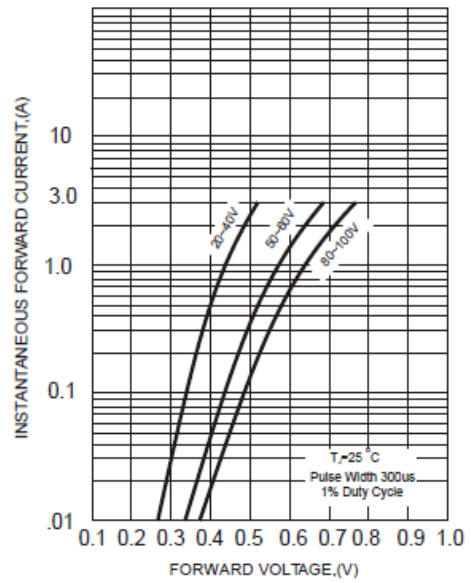


FIG.2-TYPICAL FORWARD CHARACTERISTICS

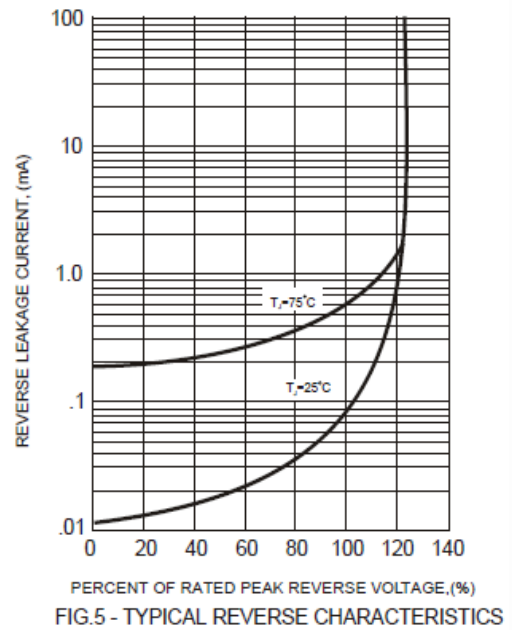
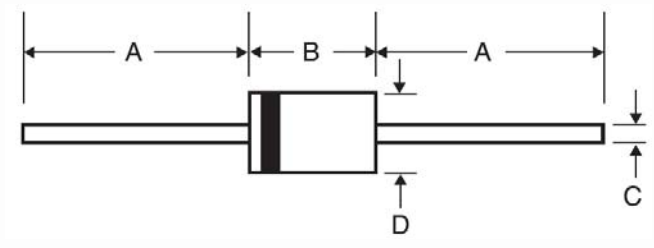


FIG.5 - TYPICAL REVERSE CHARACTERISTICS

Package Dimension

DO-201AD



Dimensions				
Symbol	Millimeters		Inches	
	Min	Max	Min	Max
A	25.40	-	1.000	-
B	7.30	9.50	0.287	0.374
C	1.20	1.30	0.047	0.051
D	4.80	5.60	0.188	0.220

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